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ABSTRACT OF THE DISCLOSURE

Methods of forming contacts, methods of contacting lines, methods of operating integrated circuitry, and related integrated circuitry constructions are described. In one embodiment, a plurality of conductive lines are formed over a substrate and diffusion regions are formed within the substrate elevationally below the lines. The individual diffusion regions are disposed proximate individual conductive line portions and collectively define therewith individual contact pads with which electrical connection is desired. Insulative material is formed over the conductive line portions and diffusion regions, with contact openings being formed therethrough to expose portions of the individual contact pads. Conductive contacts are formed within the contact openings and in electrical connection with the individual contact pads. In a preferred embodiment, the substrate and diffusion regions provide a pn junction which is configured for biasing into a reverse-biased diode configuration. In operation, the pn junction is sufficiently biased to preclude electrical shorting between the conductive line and the substrate for selected magnitudes of electrical current provided through the conductive line and the conductive material forming the conductive contacts.